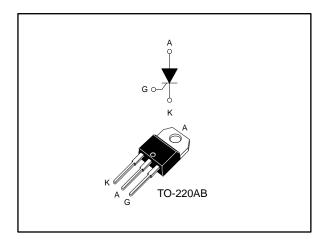


High temperature 40 A SCRs

Datasheet - production data



Features

- High junction temperature : T_j = 150 °C
- High noise immunity dV/dt = 500 V/µs up to 150 °C
- Gate triggering current I_{GT} = 15 mA
- Off-state voltage 600 V VDRM/VRRM
- High turn on current rise dl/dt = 100 A/µs
- ECOPACK[®]2 compliant component

Applications

- Motorbike voltage regulator circuits
- Inrush current limiting circuit
- Motor control circuits and starters
- Solid state relays

Description

The TN4015H-6T in non-isolated TO-220AB package offers high thermal performances up to 40 A, thanks to its junction temperature up to 150°C.

Its trade-off noise immunity (dV/dt = 500 V/ μ s) versus its gate triggering current (I_{GT} = 15 mA) and its turn-on current rise (dI/dt = 100 A/ μ s) allows to design robust and compact control circuit for voltage regulator in motorbikes and industrial drives, overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits.

Table 1: Device summary

Order code	Package	Vdrm/Vrrm	Ідт
TN4015H-6T	TO-220AB	600 V	15 mA

September 2016

DocID029585 Rev 1

www.st.com

This is information on a product in full production.

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), $T_j = 25$ °C unless otherwise specified

Symbol	Parameter	Value	Unit			
I _{T(RMS)}	RMS on-state current (180 ° conduction	T _c = 119 °C	40	А		
			T _c = 120 °C	25		
It(av)	Average on-state current (180 ° conducti	ion angle)	T _c = 125 °C	22	А	
			T _c = 128 °C	20		
Ітям	Non repetitive surge peak on state surre	nt	$t_{p} = 8.3 \text{ ms}$	394	_	
IISM	Non repetitive surge peak on-state current $t_p = 10 \text{ ms}$			360	A	
l ² t	I ² t value for fusing	648	A ² s			
dl/dt	Critical rate of rise of on-state current $I_G = 2 \text{ x } I_{GT}$, tr $\leq 100 \text{ ns}$	100	A/µs			
Vdrm/Vrrm	Repetitive peak off-state voltage	600	V			
Vdsm/Vrsm	Non repetitive surge peak off-state voltage t _p =			V _{DRM} /V _{RRM} + 100	V	
Igм	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	А	
P _{G(AV)}	Average gate power dissipation	1	W			
Vrgm	Maximum peak reverse gate voltage	5	V			
T _{stg}	Storage junction temperature range		-40 to +150	°C		
Tj	Maximum operating junction temperature		-40 to +150	°C		
ΤL	Maximum lead temperature soldering du	ring 10 s		260	°C	

Table 3: Electrical characteristics (T_j = 25 °C unless otherwise specified)

Symbol	Test Conditions		Value	Unit	
lgт	Max.				mA
V _{GT}	$V_{D} = 12 \text{ V}, \text{R}_{L} = 33 \Omega$		Max.	1.3	V
Vgd	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$	Min.	0.15	V	
Ін	I _T = 500 mA, gate open Max.				mA
١L	$I_G = 1.2 \text{ x } I_{GT}$ Max.				mA
dV/dt	$V_D = 402 V$, gate open	Min.	500	V/µs	
t _{gt}	$I_T = 80 \text{ A}, V_D = 600 \text{ V}, I_G = 100 \text{ mA}, (dI_G/dt) \text{ max} = 0.2 \text{ A}/\mu \text{s}$ Typ.				μs
tq	V_{D} = 402 V, I_{T} = 40 A, V_{R} = 25 V, dV_{D}/dt = 50 V/µs, $(dI_{G}/dt)max$ = 30 A/µs	T _j = 150 °C	Тур.	85	μs



Characteristics

Table 4:	Static	characteristics

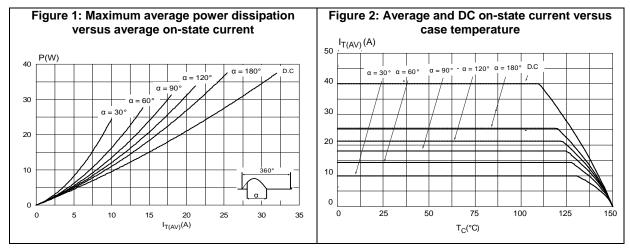
Symbol	Symbol Test conditions					
Vtm	I _{TM} = 80 A, t _p = 380 μs	T _j = 25 °C	Max.	1.6	v	
V _{TO}	Threshold voltage	T _j = 150 °C	Max.	0.85	v	
RD	Dynamic resistance	T _j = 150 °C	Max.	10	mΩ	
Idrm, Irrm		T _j = 25 °C		10	μA	
	Vd = Vdrm = Vrrm	T _j = 150 °C	Max.	6	mA	

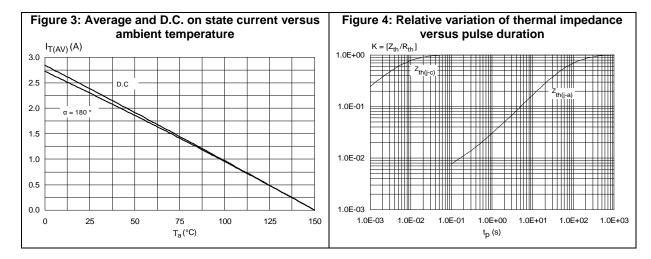
Table 5: Thermal parameters

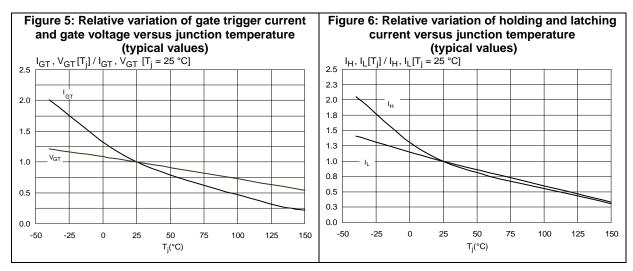
Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (DC)	0.8	0000
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W



1.1 Characteristics (curves)





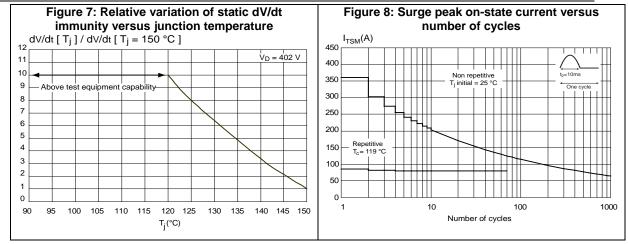


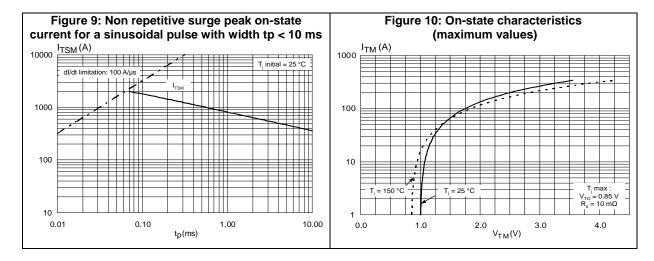
4/9

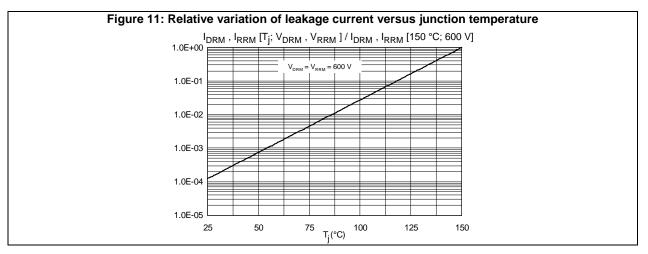
DocID029585 Rev 1



Characteristics







57

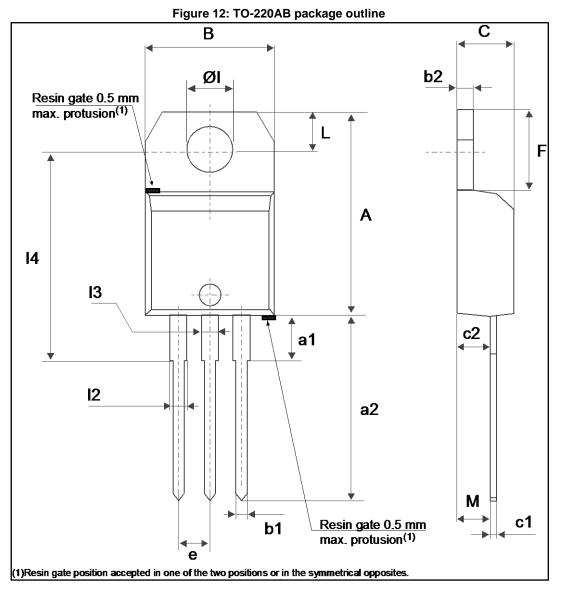
DocID029585 Rev 1

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free, halogen-free package

2.1 TO-220AB package information



DocID029585 Rev 1



6/9

Package information

Table 6: TO-220AB package mechanical data							
	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	15.20		15.90	0.5984		0.6260	
a1		3.75			0.1476		
a2	13.00		14.00	0.5118		0.5512	
В	10.00		10.40	0.3937		0.4094	
b1	0.61		0.88	0.0240		0.0346	
b2	1.23		1.32	0.0484		0.0520	
С	4.40		4.60	0.1732		0.1811	
c1	0.49		0.70	0.0193		0.0276	
c2	2.40		2.72	0.0945		0.1071	
е	2.40		2.70	0.0945		0.1063	
F	6.20		6.60	0.2441		0.2598	
ØI	3.73		3.88	0.1469		0.1528	
14	15.8	16.40	16.80	0.6220	0.6457	0.6614	
L	2.65		2.95	0.1043		0.1161	
12	1.14		1.70	0.0449		0.0669	
13	1.14		1.70	0.0449		0.0669	
М		2.60			0.1024		



3 Ordering information

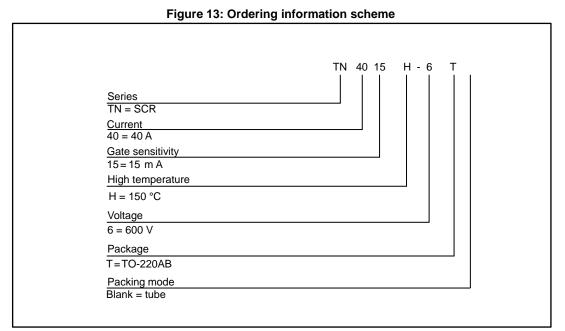


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN4015H-6T	TN4015H6	TO-220AB	2.3 g	50	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
08-Sep-2016	1	Initial release.



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